

SUBSTRATE PROPERTY	MGSi4GDFZNA _s	MGSi4GDFZNS _b	MGSi4GDFZNP	MGSi4GDFZPB
Diameter	100 mm			
Growth Method	GDFZ			
Orientation	<100>, <110>, <111>			
Carrier Type	N-type			P-type
Dopant	As	Sb	P	B
Resistivity	1000-2000 Ω·cm			
Thickness	525 μm ± 25 μm			
TTV	≤10 μm			
Bow	≤40 μm			

*The other specifications can be customized according to customer's requirements